

## Rail-to-rail CMOS quad operational amplifier

### Features

- Rail-to-rail input and output voltage ranges
- Single (or dual) supply operation from 2.7 to 16 V
- Extremely low input bias current: 1 pA typ
- Low input offset voltage: 5 mV max.
- Specified for 600  $\Omega$  and 100  $\Omega$  loads
- Low supply current: 200  $\mu$ A/ampli ( $V_{CC} = 3$  V)
- Latch-up immunity
- Spice macromodel included in this specification

### Description

The TS914 is a rail-to-rail CMOS quad operational amplifier designed to operate with a single or dual supply voltage.

The input voltage range  $V_{icm}$  includes the two supply rails  $V_{CC}^+$  and  $V_{CC}^-$ .

The output reaches  $V_{CC}^- +50$  mV,  $V_{CC}^+ -50$  mV, with  $R_L = 10$  k $\Omega$ , and  $V_{CC}^- +350$  mV,  $V_{CC}^+ -350$  mV, with  $R_L = 600$   $\Omega$ .

This product offers a broad supply voltage operating range from 2.7 to 16 V and a supply current of only 200  $\mu$ A/amp ( $V_{CC} = 3$  V).

Source and sink output current capability is typically 40 mA (at  $V_{CC} = 3$  V), fixed by an internal limitation circuit.

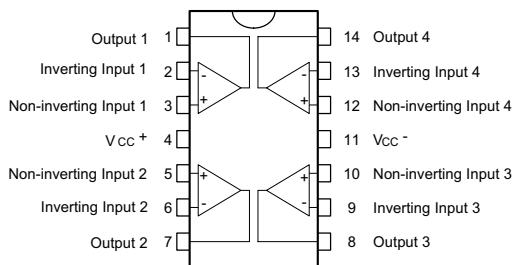


**N**  
**DIP-14**  
(Plastic package)



**D**  
**SO-14**  
(Plastic micropackage)

### Pin connections (top view)



# 1 Absolute maximum ratings and operating conditions

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{CC}$	Supply voltage <sup>(1)</sup>	18	V
$V_{id}$	Differential input voltage <sup>(2)</sup>	$\pm 18$	V
$V_i$	Input voltage <sup>(3)</sup>	-0.3 to 18	V
$I_{in}$	Current on inputs	$\pm 50$	mA
$I_o$	Current on outputs	$\pm 130$	mA
$T_j$	Maximum junction temperature	150	°C
$T_{stg}$	Storage temperature	-65 to +150	°C
$R_{thja}$	Thermal resistance junction to ambient <sup>(4)</sup> DIP14 SO-14	83 103	°C/W
$R_{thjc}$	Thermal resistance junction to case DIP14 SO-14	33 31	°C/W
ESD	HBM: human body model <sup>(5)</sup>	1	kV
	MM: machine model <sup>(6)</sup>	50	V
	CDM: charged device model <sup>(7)</sup>	1.5	kV

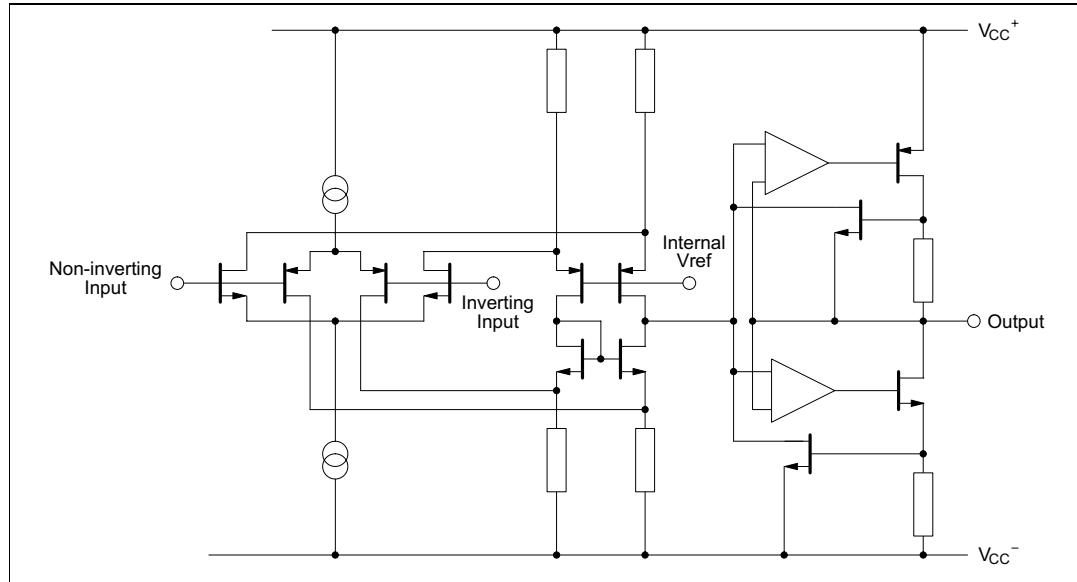
1. All voltage values, except differential voltage are with respect to network ground terminal.
2. Differential voltages are the non-inverting input terminal with respect to the inverting input terminal.
3. The magnitude of input and output voltages must never exceed  $V_{CC}^+ + 0.3$  V.
4. Short-circuits can cause excessive heating. Destructive dissipation can result from simultaneous short-circuit on all amplifiers. These are typical values.
5. Human body model: a 100 pF capacitor is charged to the specified voltage, then discharged through a 1.5kΩ resistor between two pins of the device. This is done for all couples of connected pin combinations while the other pins are floating.
6. Machine model: a 200 pF capacitor is charged to the specified voltage, then discharged directly between two pins of the device with no external series resistor (internal resistor < 5 Ω). This is done for all couples of connected pin combinations while the other pins are floating.
7. Charged device model: all pins and the package are charged together to the specified voltage and then discharged directly to the ground through only one pin. This is done for all pins.

**Table 2. Operating conditions**

Symbol	Parameter	Value	Unit
$V_{CC}$	Supply voltage	2.7 to 16	V
$V_{icm}$	Common mode input voltage range	$V_{CC}^- - 0.2$ to $V_{CC}^+ + 0.2$	V
$T_{oper}$	Operating free air temperature range	-40 to + 125	°C

## 2 Typical application information

Figure 1. Schematic diagram



### 3 Electrical characteristics

**Table 3.**  $V_{CC}^+ = 3\text{ V}$ ,  $V_{CC}^- = 0\text{ V}$ ,  $R_L$ ,  $C_L$  connected to  $V_{CC}/2$ ,  $T_{amb} = 25^\circ\text{ C}$  (unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{io}$	Input offset voltage ( $V_{icm} = V_o = V_{CC}/2$ )	TS914 TS914A $T_{min} \leq T_{amb} \leq T_{max}$ , TS914 $T_{min} \leq T_{amb} \leq T_{max}$ , TS914A			10 5 12 7	mV
$\Delta V_{io}$	Input offset voltage drift			5		$\mu\text{V}/^\circ\text{C}$
$I_{io}$	Input offset current <sup>(1)</sup>	$T_{min} \leq T_{amb} \leq T_{max}$		1	100 200	pA
$I_{ib}$	Input bias current <sup>(1)</sup>	$T_{min} \leq T_{amb} \leq T_{max}$		1	150 300	pA
$I_{CC}$	Supply current	per amplifier, $A_{VCL} = 1$ , no load $T_{min} \leq T_{amb} \leq T_{max}$		200	300 400	$\mu\text{A}$
CMR	Common mode rejection ratio	$V_{ic} = 0$ to $3\text{ V}$ , $V_o = 1.5\text{ V}$		70		dB
SVR	Supply voltage rejection ratio	$V_{CC}^+ = 2.7$ to $3.3\text{ V}$ , $V_o = V_{CC}/2$		80		dB
$A_{vd}$	Large signal voltage gain	$R_L = 10\text{ k}\Omega$ $V_o = 1.2\text{ V}$ to $1.8\text{ V}$ $T_{min} \leq T_{amb} \leq T_{max}$	3 2	10		V/mV
$V_{OH}$	High level output voltage	$V_{id} = 1\text{ V}$ , $R_L = 10\text{ k}\Omega$ $R_L = 600\text{ }\Omega$ $R_L = 100\text{ }\Omega$ $V_{id} = 1\text{ V}$ , $T_{min} \leq T_{amb} \leq T_{max}$ $R_L = 10\text{ k}\Omega$ $R_L = 600\text{ }\Omega$	2.9 2.2 2.8 2.1	2.97 2.7 2		V
$V_{OL}$	Low level output voltage	$V_{id} = -1\text{ V}$ , $R_L = 10\text{ k}\Omega$ $R_L = 600\text{ }\Omega$ $R_L = 100\text{ }\Omega$ $V_{id} = -1\text{ V}$ , $T_{min} \leq T_{amb} \leq T_{max}$ $R_L = 10\text{ k}\Omega$ $R_L = 600\text{ }\Omega$		50 300 900	100 600 150 900	mV
$I_o$	Output short circuit current	$V_{id} = \pm 1\text{ V}$ Source ( $V_o = V_{CC}$ ) Sink ( $V_o = V_{CC}^+$ )		40 40		mA
GBP	Gain bandwidth product	$A_{VCL} = 100$ , $R_L = 10\text{ k}\Omega$ $C_L = 100\text{ pF}$ , $f = 100\text{ kHz}$		0.8		MHz
SR	Slew rate	$A_{VCL} = 1$ , $R_L = 10\text{ k}\Omega$ $C_L = 100\text{ pF}$ , $V_i = 1.3\text{ V}$ to $1.7\text{ V}$		0.5		V/ $\mu\text{s}$
$\phi_m$	Phase margin			30		°
$e_n$	Equivalent input noise voltage	$R_s = 100\text{ }\Omega$ $f = 1\text{ kHz}$		30		nV/ $\sqrt{\text{Hz}}$
$V_{O1}/V_{O2}$	Channel separation	$f = 1\text{ kHz}$		120		dB

1. Maximum values include unavoidable inaccuracies of the industrial tests.

**Table 4.**  $V_{CC}^+ = 5 \text{ V}$ ,  $V_{CC}^- = 0 \text{ V}$ ,  $R_L$ ,  $C_L$  connected to  $V_{CC}/2$ ,  $T_{amb} = 25^\circ \text{ C}$  (unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{io}$	Input offset voltage ( $V_{icm} = V_o = V_{CC}/2$ )	TS914 TS914A $T_{min} \leq T_{amb} \leq T_{max}$ , TS914 $T_{min} \leq T_{amb} \leq T_{max}$ , TS914A			10 5 12 7	mV
$\Delta V_{io}$	Input offset voltage drift			5		$\mu\text{V}/^\circ\text{C}$
$I_{io}$	Input offset current <sup>(1)</sup>	$T_{min} \leq T_{amb} \leq T_{max}$		1	100 200	pA
$I_{ib}$	Input bias current <sup>(1)</sup>	$T_{min} \leq T_{amb} \leq T_{max}$		1	150 300	pA
$I_{cc}$	Supply current	per amplifier, $A_{VCL} = 1$ , no load $T_{min} \leq T_{amb} \leq T_{max}$		230	350 450	$\mu\text{A}$
CMR	Common mode rejection ratio	$V_{ic} = 1.5$ to $3 \text{ V}$ , $V_o = 2.5 \text{ V}$		85		dB
SVR	Supply voltage rejection ratio	$V_{CC}^+ = 3$ to $5 \text{ V}$ , $V_o = V_{CC}/2$		80		dB
$A_{vd}$	Large signal voltage gain	$R_L = 10 \text{ k}\Omega$ $V_o = 1.5 \text{ V}$ to $3.5 \text{ V}$ $T_{min} \leq T_{amb} \leq T_{max}$	10 7	40		$\text{V/mV}$
$V_{OH}$	High level output voltage	$V_{id} = 1 \text{ V}$ , $R_L = 10 \text{ k}\Omega$ $R_L = 600 \Omega$ $R_L = 100 \Omega$ $V_{id} = 1 \text{ V}$ , $T_{min} \leq T_{amb} \leq T_{max}$ $R_L = 10 \text{ k}\Omega$ $R_L = 600 \Omega$	4.85 4.20  4.8 4.1	4.95 4.65 3.7		V
$V_{OL}$	Low level output voltage	$V_{id} = -1 \text{ V}$ , $R_L = 10 \text{ k}\Omega$ $R_L = 600 \Omega$ $R_L = 100 \Omega$ $V_{id} = -1 \text{ V}$ , $T_{min} \leq T_{amb} \leq T_{max}$ $R_L = 10 \text{ k}\Omega$ $R_L = 600 \Omega$		50 350 1400	100 680  150 900	$\text{mV}$
$I_o$	Output short circuit current	$V_{id} = \pm 1 \text{ V}$ Source ( $V_o = V_{CC}$ ) Sink ( $V_o = V_{CC}^+$ )		60 60		mA
GBP	Gain bandwidth product	$A_{VCL} = 100$ , $R_L = 10 \text{ k}\Omega$ $C_L = 100 \text{ pF}$ , $f = 100 \text{ kHz}$		1		MHz
SR	Slew rate	$A_{VCL} = 1$ , $R_L = 10 \text{ k}\Omega$ $C_L = 100 \text{ pF}$ , $V_i = 1 \text{ V}$ to $4 \text{ V}$		0.8		$\text{V}/\mu\text{s}$
$\phi_m$	Phase margin			30		°
$e_n$	Equivalent input noise voltage	$R_s = 100 \Omega$ , $f = 1 \text{ kHz}$		30		$\text{nV}/\sqrt{\text{Hz}}$
$V_{O1}/V_{O2}$	Channel separation	$f = 1 \text{ kHz}$		120		dB

1. Maximum values include unavoidable inaccuracies of the industrial tests.

**Table 5.**  $V_{CC}^+ = 10 \text{ V}$ ,  $V_{DD} = 0 \text{ V}$ ,  $R_L$ ,  $C_L$  connected to  $V_{CC}/2$ ,  $T_{amb} = 25^\circ \text{ C}$   
(unless otherwise specified)

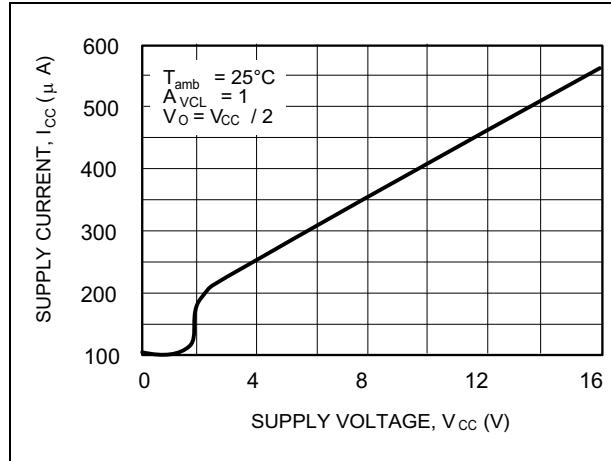
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{io}$	Input offset voltage ( $V_{icm} = V_o = V_{CC}/2$ )	TS914 TS914A $T_{min} \leq T_{amb} \leq T_{max}$ , TS914 $T_{min} \leq T_{amb} \leq T_{max}$ , TS914A			10 5 12 7	mV
$\Delta V_{io}$	Input offset voltage drift			5		$\mu\text{V}/^\circ\text{C}$
$I_{io}$	Input offset current <sup>(1)</sup>	$T_{min} \leq T_{amb} \leq T_{max}$		1	100 200	pA
$I_{ib}$	Input bias current <sup>(1)</sup>	$T_{min} \leq T_{amb} \leq T_{max}$		1	150 300	pA
CMR	Common mode rejection ratio	$V_{ic} = 3 \text{ to } 7 \text{ V}$ , $V_o = 5 \text{ V}$ $V_{ic} = 0 \text{ to } 10 \text{ V}$ , $V_o = 5 \text{ V}$		90 75		dB
SVR	Supply voltage rejection ratio	$V_{CC}^+ = 5 \text{ to } 10 \text{ V}$ , $V_o = V_{CC}/2$		90		dB
$A_{vd}$	Large signal voltage gain	$R_L = 10 \text{ k}\Omega$ , $V_o = 2.5 \text{ V to } 7.5 \text{ V}$ $T_{min} \leq T_{amb} \leq T_{max}$	15 10	60		V/mV
$V_{OH}$	High level output voltage	$V_{id} = 1 \text{ V}$ , $R_L = 10 \text{ k}\Omega$ $R_L = 600 \Omega$ $R_L = 100 \Omega$ $V_{id} = 1 \text{ V}$ , $T_{min} \leq T_{amb} \leq T_{max}$ $R_L = 10 \text{ k}\Omega$ $R_L = 600 \Omega$	9.85 9	9.95 9.35 7.8		V
$V_{OL}$	Low level output voltage	$V_{id} = -1 \text{ V}$ , $R_L = 10 \text{ k}\Omega$ $R_L = 600 \Omega$ $R_L = 100 \Omega$ $V_{id} = -1 \text{ V}$ , $T_{min} \leq T_{amb} \leq T_{max}$ $R_L = 10 \text{ k}\Omega$ $R_L = 600 \Omega$		50 650 2300	180 800 150 900	mV
$I_o$	Output short circuit current	$V_{id} = \pm 1 \text{ V}$		60		mA
$I_{CC}$	Supply current / operator	$A_{VCL} = 1$ , no load, $T_{min} \leq T_{amb} \leq T_{max}$		400	600 700	$\mu\text{A}$
GBP	Gain bandwidth product	$A_{VCL} = 100$ , $R_L = 10 \text{ k}\Omega$ , $C_L = 100 \text{ pF}$ , $f = 100 \text{ kHz}$		1.4		MHz
SR	Slew rate	$A_{VCL} = 1$ , $R_L = 10 \text{ k}\Omega$ , $C_L = 100 \text{ pF}$ , $V_i = 2.5 \text{ V to } 7.5 \text{ V}$		1		V/ $\mu\text{s}$
$\phi_m$	Phase margin	$R_s = 100 \Omega$ , $f = 1 \text{ kHz}$		40		°
$e_n$	Equivalent input noise voltage	$R_s = 100 \Omega$ , $f = 1 \text{ kHz}$		30		nV/ $\sqrt{\text{Hz}}$
THD	Total harmonic distortion	$A_{VCL} = 1$ , $R_L = 10 \text{ k}\Omega$ , $C_L = 100 \text{ pF}$ , $V_o = 4.75 \text{ to } 5.25 \text{ V}$ , $f = 1 \text{ kHz}$		0.02		%
$C_{in}$	Input capacitance			1.5		pF

**Table 5.**  $V_{CC}^+ = 10$  V,  $V_{DD} = 0$  V,  $R_L$ ,  $C_L$  connected to  $V_{CC}/2$ ,  $T_{amb} = 25^\circ$  C  
(unless otherwise specified) (continued)

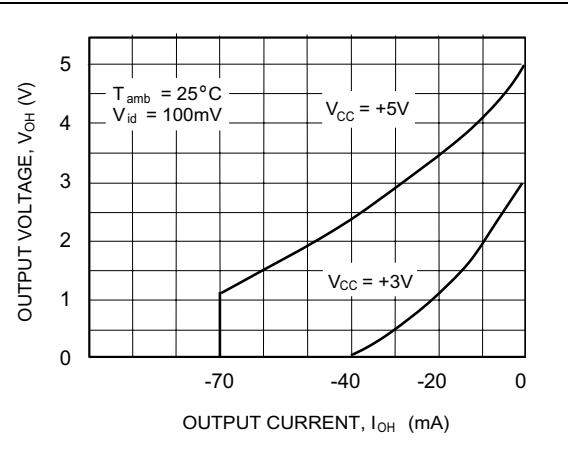
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$R_{in}$	Input resistance			>10		Tera $\Omega$
$V_{O1}/V_{O2}$	Channel separation	$f = 1$ kHz		120		dB

1. Maximum values include unavoidable inaccuracies of the industrial tests.

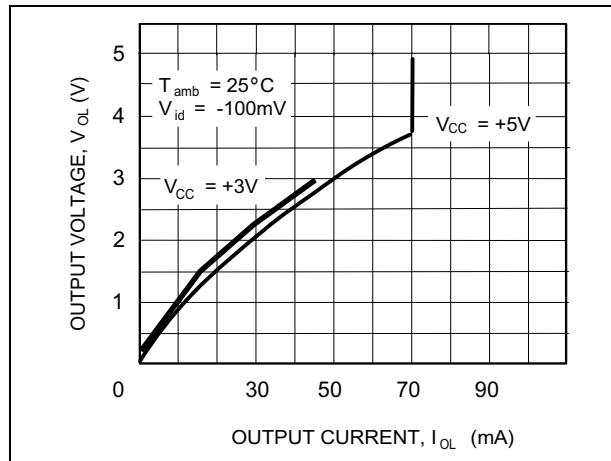
**Figure 2.** Supply current (each amplifier) vs. supply voltage



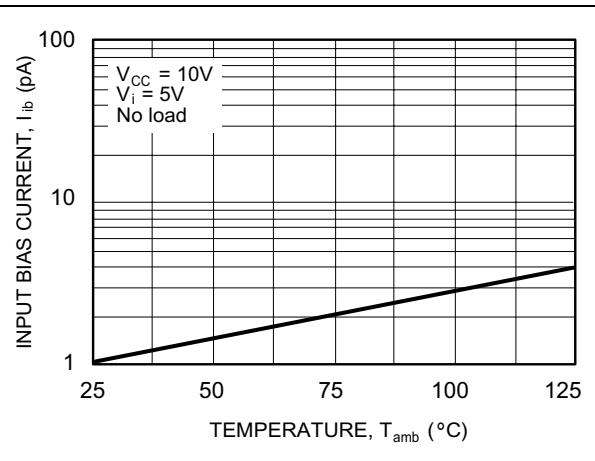
**Figure 3.** High level output voltage vs. high level output current



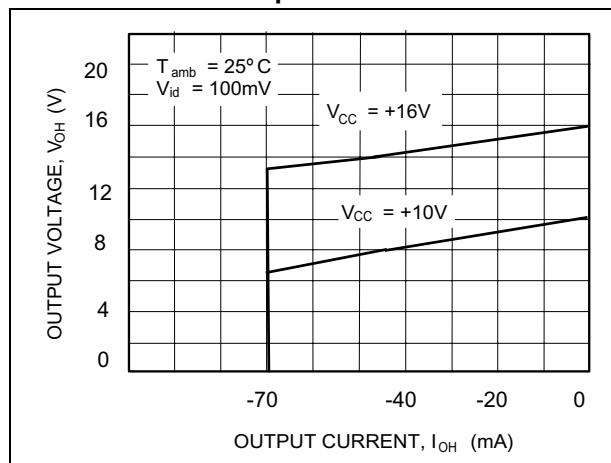
**Figure 4.** Low level output voltage vs. low level output current



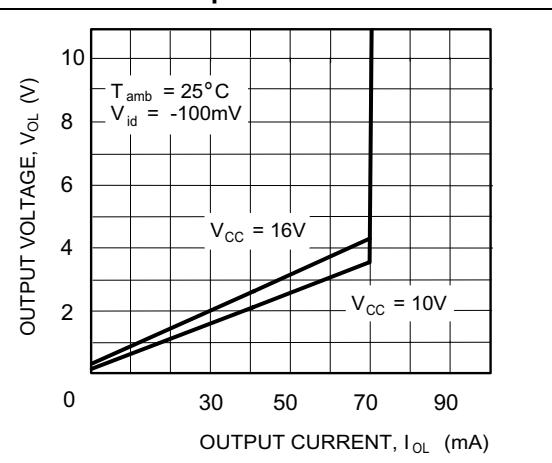
**Figure 5.** Input bias current vs. temperature

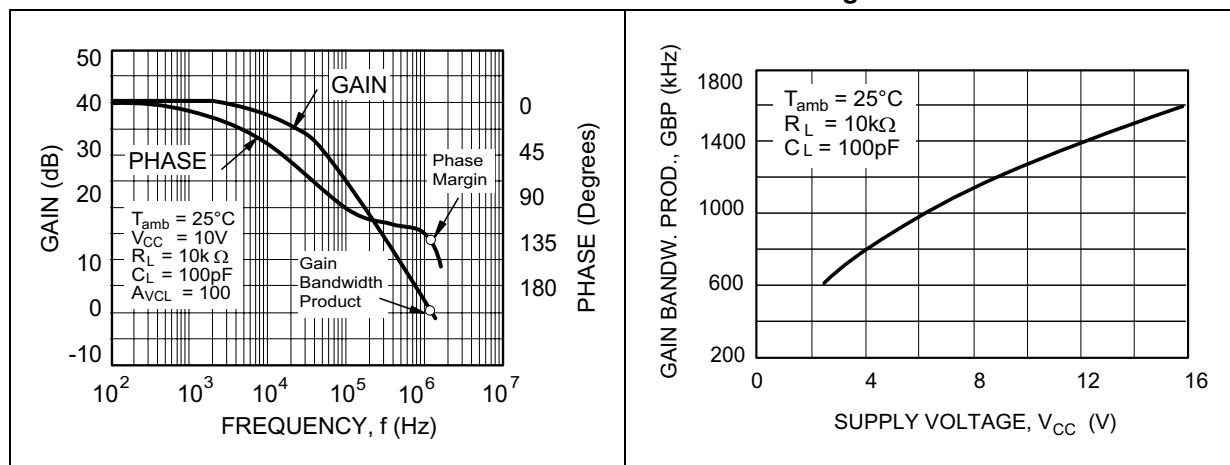
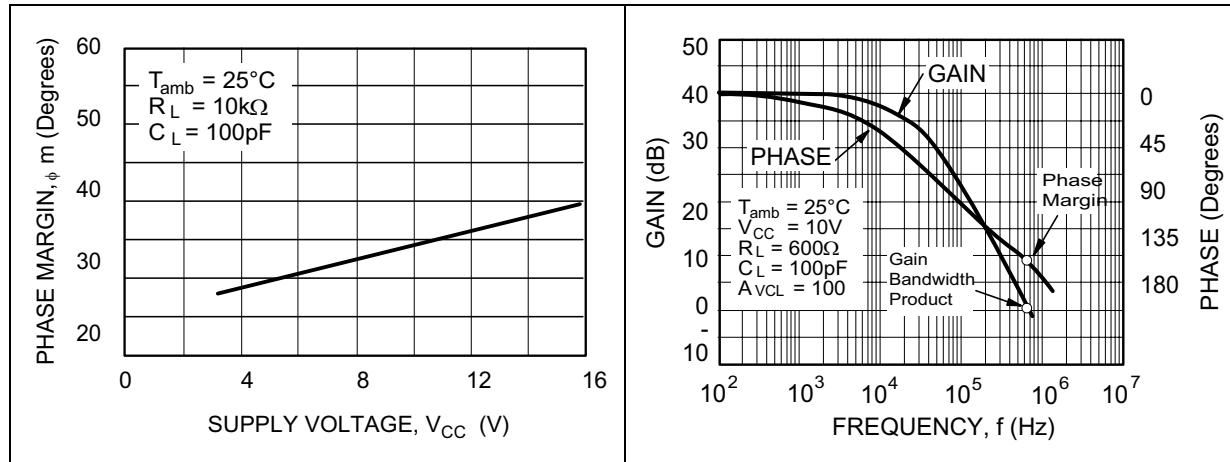
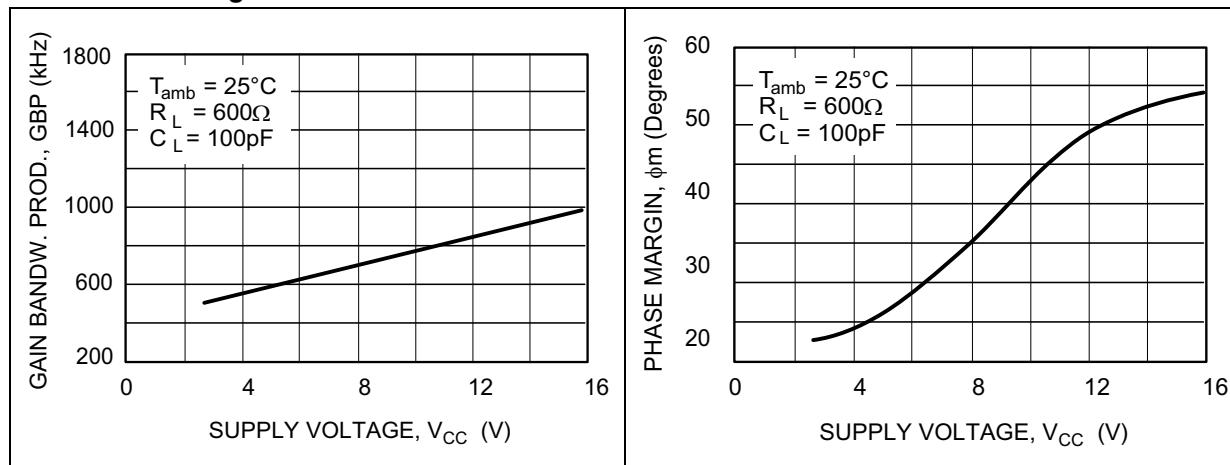
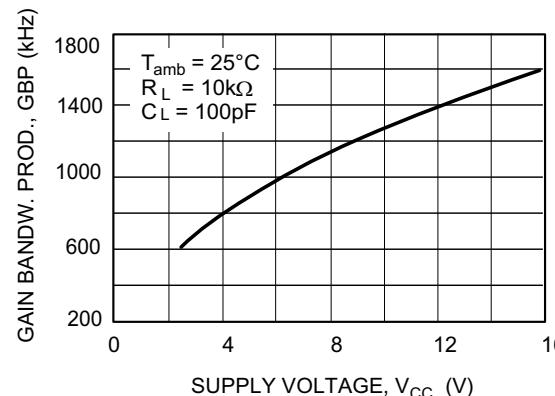
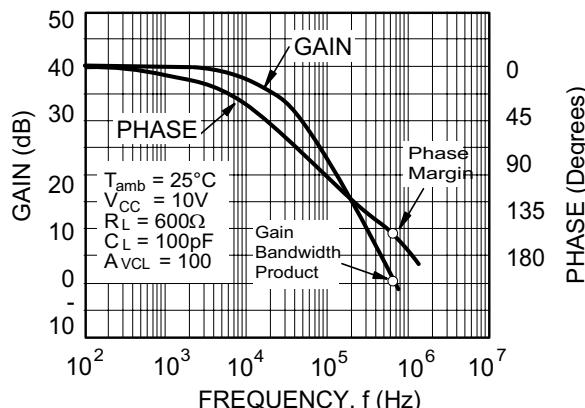
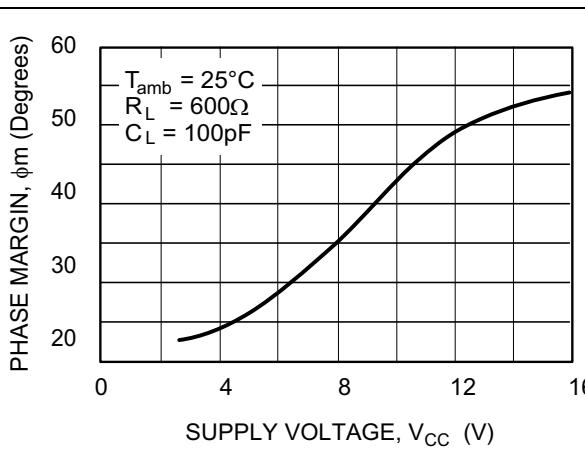


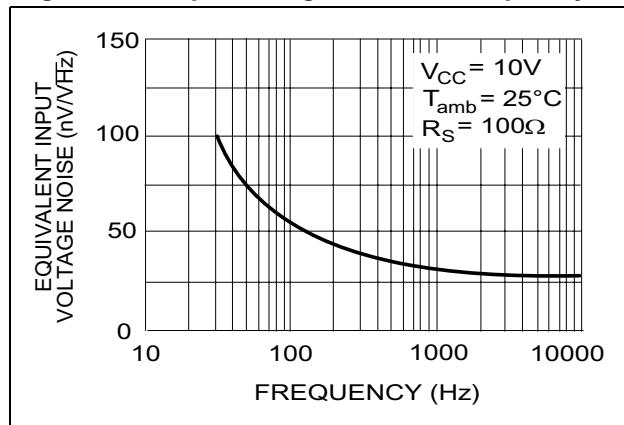
**Figure 6.** High level output voltage vs. high level output current



**Figure 7.** Low level output voltage vs. low level output current



**Figure 8. Gain and phase vs. frequency****Figure 10. Phase margin vs. supply voltage****Figure 12. Gain bandwidth product vs. supply voltage****Figure 9. Gain bandwidth product vs. supply voltage****Figure 11. Gain and phase vs. frequency****Figure 13. Phase margin vs. supply voltage**

**Figure 14. Input voltage noise vs. frequency**

## 4 Macromodels

### 4.1 Important note concerning this macromodel

- All models are a trade-off between accuracy and complexity (that is, simulation time). Macromodels are not a substitute for breadboarding; rather, they confirm the validity of a design approach and help to select surrounding component values.
- A macromodel emulates the **nominal** performance of a **typical** device within **specified operating conditions** (such as temperature or supply voltage, etc). Thus, the macromodel is often not as exhaustive as the datasheet, its purpose is to illustrate the main parameters of the product.
- Data derived from macromodels used outside of the specified conditions (such as  $V_{CC}$ , or temperature) or even worse, outside of the device's operating conditions (such as  $V_{CC}$  or  $V_{icm}$ ) is not reliable in any way.

The values provided in *Table 6* are derived from this macromodel.

**Table 6.**  $V_{CC^+} = 3$  V,  $V_{CC^-} = 0$  V,  $R_L$ ,  $C_L$  connected to  $V_{CC}/2$ ,  $T_{amb} = 25^\circ$  C  
(unless otherwise specified)

Symbol	Conditions	Value	Unit
$V_{io}$		0	mV
$A_{vd}$	$R_L = 10$ kΩ	10	V/mV
$I_{CC}$	No load, per operator	100	µA
$V_{icm}$		-0.2 to 3.2	V
$V_{OH}$	$R_L = 600$ Ω	2.96	V
$V_{OL}$	$R_L = 60$ Ω	300	mV
$I_{sink}$	$V_O = 3$ V	40	mA
$I_{source}$	$V_O = 0$ V	40	mA
GBP	$R_L = 10$ kΩ $C_L = 100$ pF	0.8	MHz
SR	$R_L = 10$ kΩ $C_L = 100$ pF	0.3	V/µs
$\phi_m$	Phase margin	30	Degrees

## 4.2 Macromodel code

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* Standard Linear Ics Macromodels, 1993.
** CONNECTIONS :
* 1 INVERTING INPUT
* 2 NON-INVERTING INPUT
* 3 OUTPUT
* 4 POSITIVE POWER SUPPLY
* 5 NEGATIVE POWER SUPPLY
*
.SUBCKT TS914 1 2 3 4 5
*****
.MODEL MDTH D IS=1E-8 KF=6.564344E-14 CJO=10F
CIP 2 5 1.000000E-12
CIN 1 5 1.000000E-12
EIP 10 5 2 5 1
EIN 16 5 1 5 1
RIP 10 11 6.500000E+00
RIN 15 16 6.500000E+00
RIS 11 15 7.322092E+00
DIP 11 12 MDTH 400E-12
DIN 15 14 MDTH 400E-12
VOFP 12 13 DC 0.000000E+00
VOFN 13 14 DC 0
IPOL 13 5 4.000000E-05
CPS 11 15 2.498970E-08
DINN 17 13 MDTH 400E-12
VIN 17 5 0.000000e+00
DINR 15 18 MDTH 400E-12
VIP 4 18 0.000000E+00
FCP 4 5 VOFP 5.750000E+00
FCN 5 4 VOFN 5.750000E+00
* AMPLIFYING STAGE
FIP 5 19 VOFP 4.400000E+02
FIN 5 19 VOFN 4.400000E+02
RG1 19 5 4.904961E+05
RG2 19 4 4.904961E+05
CC 19 29 2.200000E-08
HZTP 30 29 VOFP 1.8E+03
HZTN 5 30 VOFN 1.8E+03
DOPM 19 22 MDTH 400E-12
DONM 21 19 MDTH 400E-12
HOPM 22 28 VOUT 3800
VIPM 28 4 230
HONM 21 27 VOUT 3800
VINM 5 27 230
EOUT 26 23 19 5 1
VOUT 23 5 0
ROUT 26 3 82
COUT 3 5 1.000000E-12
DOP 19 68 MDTH 400E-12
VOP 4 25 1.724

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```
HSCP 68 25 VSCP1 0.8E+8
DON 69 19 MDTH 400E-12
VON 24 5 1.7419107
HSCN 24 69 VSCN1 0.8E+8
VSCTHP 60 61 0.0875
DSCP1 61 63 MDTH 400E-12
VSCP1 63 64 0
ISCP 64 0 1.000000E-8
DSCP2 0 64 MDTH 400E-12
DSCN2 0 74 MDTH 400E-12
ISCN 74 0 1.000000E-8
VSCN1 73 74 0
DSCN1 71 73 MDTH 400E-12
VSCTHN 71 70 -0.55
ESCP 60 0 2 1 500
ESCN 70 0 2 1 -2000
.ENDS
```

## 5 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com).  
ECOPACK® is an ST trademark.

## 5.1 DIP14 package information

Figure 15. DIP14 package mechanical drawing

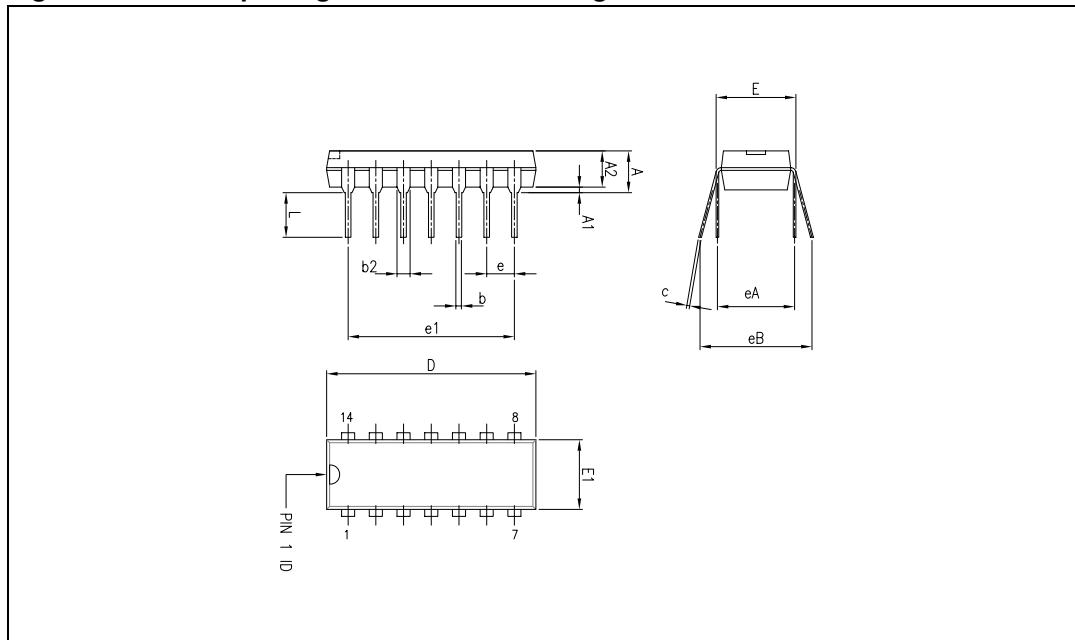


Table 7. DIP14 package mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			5.33			0.21
A1	0.38			0.015		
A2	2.92	3.30	4.95	0.11	0.13	0.19
b	0.36	0.46	0.56	0.014	0.018	0.022
b2	1.14	1.52	1.78	0.04	0.06	0.07
c	0.20	0.25	0.36	0.007	0.009	0.01
D	18.67	19.05	19.69	0.73	0.75	0.77
E	7.62	7.87	8.26	0.30	0.31	0.32
E1	6.10	6.35	7.11	0.24	0.25	0.28
e		2.54			0.10	
e1		15.24			0.60	
eA		7.62			0.30	
eB			10.92			0.43
L	2.92	3.30	3.81	0.11	0.13	0.15

## 5.2 SO-14 package information

Figure 16. SO-14 package mechanical drawing

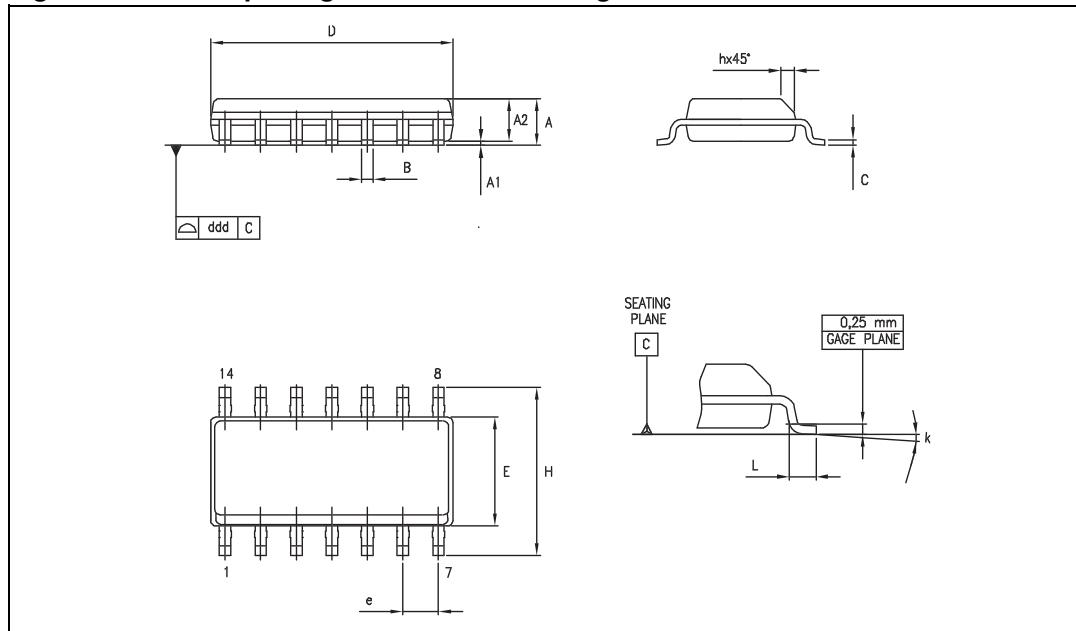


Table 8. SO-14 package mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.35		1.75	0.05		0.068
A1	0.10		0.25	0.004		0.009
A2	1.10		1.65	0.04		0.06
B	0.33		0.51	0.01		0.02
C	0.19		0.25	0.007		0.009
D	8.55		8.75	0.33		0.34
E	3.80		4.0	0.15		0.15
e		1.27			0.05	
H	5.80		6.20	0.22		0.24
h	0.25		0.50	0.009		0.02
L	0.40		1.27	0.015		0.05
k	8° (max.)					
ddd			0.10			0.004

## 6 Ordering information

**Table 9. Order codes**

Order code	Temperature range	Package	Packing	Marking
TS914IN	-40, +125° C	DIP14	Tube	TS914IN
TS914ID		SO-14	Tube and tape & reel	914I
TS914IDT		DIP14	Tube	TS914AIN
TS914AIN		SO-14	Tube and tape & reel	914AI
TS914AID		SO-14 (Automotive grade level)	Tube and tape & reel	914IY
TS914AIDT		SO-14 (Automotive grade level)	Tube and tape & reel	914AIY
TS914IYD <sup>(1)</sup>				
TS914IYDT <sup>(1)</sup>				
TS914AIYD <sup>(1)</sup>				
TS914AIYDT <sup>(1)</sup>				

1. Qualified and characterized according to AEC Q100 and Q003 or equivalent, advanced screening according to AEC Q001 & Q 002 or equivalent.

## 7 Revision history

**Table 10. Document revision history**

Date	Revision	Changes
01-Dec-2001	1	Initial release.
01-Nov-2004	2	Changed $V_{io}$ max. on cover page from 2 mV to 5 mV.
01-Jun-2005	3	Inserted PIPAP references (see order code table on cover page).
01-Feb-2006	4	Added parameters in <i>Table 1: Absolute maximum ratings on page 2</i> ( $T_j$ , ESD, $R_{thja}$ , $R_{thjc}$ ).
08-Jan-2007	5	Corrected package names in order codes table on cover page. Corrected macromodel.
02-Apr-2009	6	Minor text edits. Removed table of contents. Updated package information in <i>Chapter 5</i> . Moved <i>Table 9: Order codes</i> from cover page to end of datasheet. Added footnote to <i>Table 9: Order codes</i> .

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